

SEMITOP[®]4

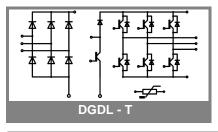
3-phase bridge rectifier + brake chopper + 3-phase bridge inverter sk 25 DGDL 12T4 T

Target Data

Features

- One screw mounting module
- Fully compatible with SEMITOP[®]1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench4 IGBT technology
- CAL4 technology free-wheeling diode
- Integrated NTC temperature sensor

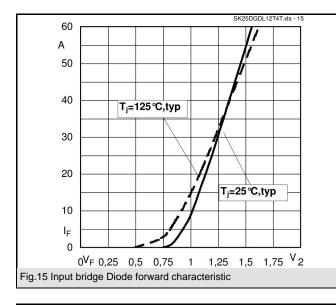
1) $V_{CE,sat}$, V_F = chip level value

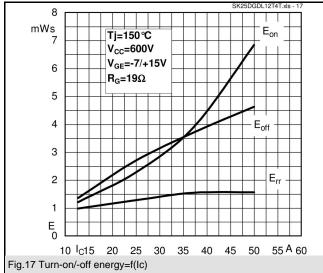


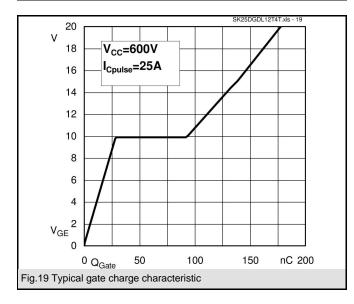
Absolute	Maximum Ratings	Ts = 25 °C	s = 25 °C, unless otherwise specified			
	Conditions	1	Values		Units	
-	verter,Chopper					
V _{CES}		1	1200		V	
I _C	T _s = 25 (70) °C		45 (36)		А	
I _{CRM}	$I_{CRM} = 3 \times I_{Cnom}, t_p = 1 \text{ ms}$		75		А	
V _{GES}			± 20		V	
T _j			-40 +175		°C	
Diode - Ir	verter,Chopper	•				
I _F	T _s = 25 (70) °C		30 (24)			
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 \text{ ms}$		75		Α	
T _i	····· ··· ·		-40 +150		°C	
Rectifier		1				
V _{RRM}			1600		V	
I _F	T _s = 70 °C		46		А	
I _{FSM} / I _{TSM}	t _p = 10 ms , sin 180 ° ,T _j = 25 °C		370			
l ² t	t _p = 10 ms , sin 180 ° ,T _j = 25 °C		684		A²s	
т _ј			-40 +175		°C	
T _{sol}	Terminals, 10 s		260		°C	
T _{stg}			-40 +125			
V _{isol}	AC, 1 min. / 1 s		2500 / 3000 V			
Characte	ristics	Ts = 25 °C	, unless ot	herwise sp	ecitied	
Symbol	Conditions	min.	typ.	max.	Units	
IGBT - Inv						
V _{CEsat}	I _C = 25 A, T _j = 25 (150) °C		1,85 (2,25)	2,05 (2,45)	V	
V _{GE(th)}	$V_{GE} = V_{CE}, I_C = 1 \text{ mA}$	5	5,8	6,5	V	
V _{CE(TO)}	T _j = 25 °C (150) °C		1,1 (1)	1,3 (1,2)	V	
r _T	T _j = 25 °C (150) °C		30 (50)		mΩ	
C _{ies}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		1,43		nF	
C _{oes}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,11		nF	
C _{res}	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,085		nF	
R _{th(j-s)}	per IGBT		0,96		K/W	
t _{d(on)}	under following conditions		22		ns	
t _r	$V_{CC} = 600 \text{ V}, V_{GE} = \pm 15 \text{ V}$		19,5		ns	
t _{d(off)}	$I_{\rm C} = 25 \text{ A}, T_{\rm j} = 150 ^{\circ}\text{C}$		288		ns	
t _f	$R_{Gon} = R_{Goff} = 19 \Omega$		77,5		ns	
E _{on}	inductive load		2,27		mJ	
E _{off}			2,7		mJ	
	verter,Chopper				1.	
$V_F = V_{EC}$	I _F = 25 A, T _j = 25(150) °C		2,4 (2,45)		V	
V _(TO)	T _j = 25 °C (150) °C		1,3 (0,9)	1,5 (1,1)	V	
r _T	T _j = 25 °C (150) °C		44 (62)	50 (68)	mΩ	
R _{th(j-s)}	per diode		1,7		K/W	
	under following conditions				Α	

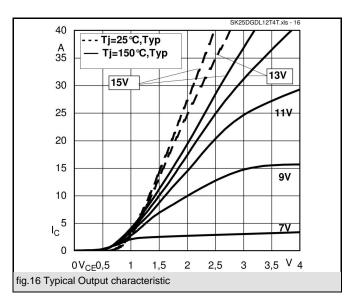
ui(j=5)			
I _{RRM}	under following conditions	-	A
Q _{rr}	$I_F = A, V_R = V$	-	μC
E _{rr}	V _{GE} = 0 V, T _j = 150 °C		mJ
	di _F /dt = - A/µs		
Diode -	Rectifier	·	
V _F	I _F = 25 A, T _i = 25() °C	1,1	V
V _(TO)	T _i = 150 °C	0,8	V
r _T	T _j = 150 °C	13	mΩ
R _{th(j-s)}	per diode	1,25	K/W
Tempe	ratur sensor		
R _{ts}	5 %, T _r = 25 (100) °C	5000(493)	Ω
Mechar	nical data	·	
w		60	g
Ms	Mounting torque	3,5	Nm

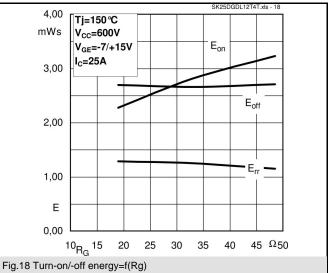
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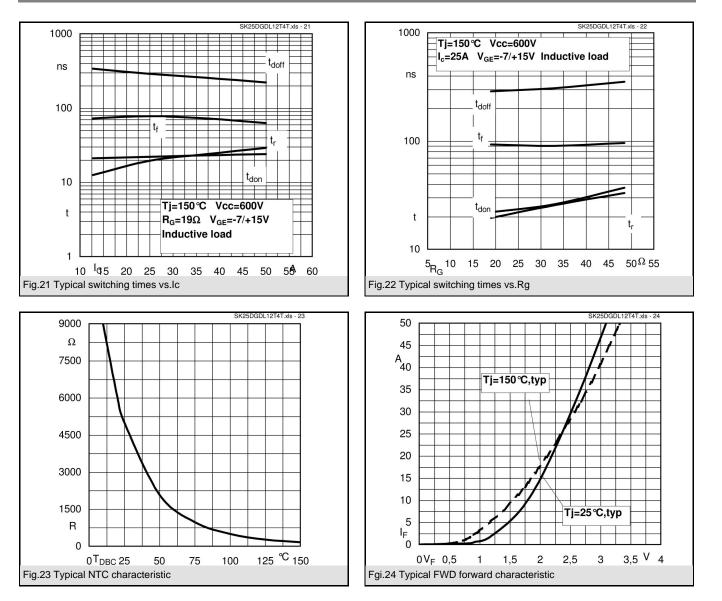






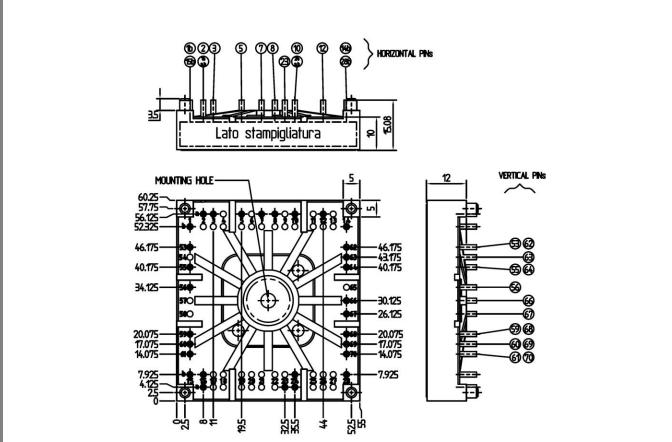




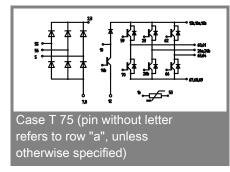


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Dimensions in mm



Case T 75 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm)



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.